

ABSTRACT OF THE DISCLOSURE

In a semiconductor substrate for use in a semiconductor device in which first device components
5 are disposed on an insulating material and second device components are fabricated, a thermal-oxide layer of 10 μm or more in thickness is formed in a region where the first device components are to be disposed, and a groove packed with a polycrystalline
10 semiconductor is formed at an inward position from the peripheral edge of the thermal-oxide layer and along the same peripheral edge. A process for manufacturing this semiconductor substrate is also disclosed.